

SN74AHC1G00 シングル、2 入力、正論理 NAND ゲート

1 特長

- 動作範囲：2V～5.5V
- 最大 t_{pd} 6.5ns (5V 時)
- 低い消費電力： $I_{CC} = 10\mu A$ (最大値)
- $\pm 8mA$ の出力駆動能力 (5V 時)
- すべての入力におけるシュミット・トリガ動作により、回路は低速の入力立ち上がり / 立ち下がり時間に対する耐性を備える
- JESD 17 準拠で 250mA 超のラッチアップ性能

2 アプリケーション

- デジタル信号のイネーブルまたはディセーブル
- インジケータ LED の制御
- 通信モジュールとシステム・コントローラの間のレベル変換

3 概要

SN74AHC1G00 は、ブール関数

$Y = \overline{A \cdot B}$ 、または $Y = \overline{A} + \overline{B}$ を正論理で実行します。

パッケージ情報

部品番号	パッケージ ⁽¹⁾	パッケージ・サイズ ⁽²⁾	本体サイズ ⁽²⁾
SN74AHC1G00	DBV (SOT-23、5)	2.9mm × 2.8mm	2.9mm × 1.6mm
	DCK (SC-70、5)	2mm × 2.1mm	2mm × 1.25mm
	DRL (SOT、5)	1.6mm × 1.6mm	1.6mm × 1.2mm

- 利用可能なすべてのパッケージについては、データシートの末尾にある注文情報を参照してください。
- パッケージ・サイズ (長さ×幅) は公称値で、該当する場合はピンも含まれます。



論理図 (正論理)



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4 Pin Configuration and Functions

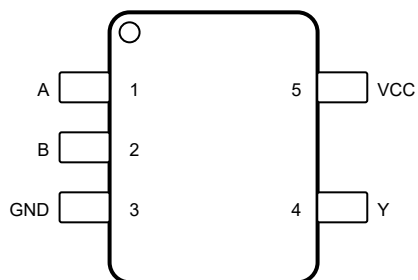


図 4-1. DBV Package 5-Pin SOT-23 Top View

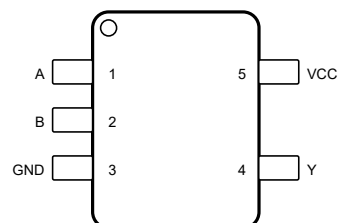


図 4-2. DCK Package 5-Pin SC70 Top View

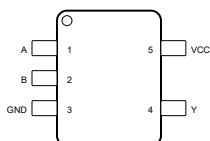


図 4-3. DRL Package 5-Pin SOT Top View

表 4-1. Pin Functions

PIN		TYPE ⁽¹⁾	DESCRIPTION
NO.	NAME		
1	A	I	A input
2	B	I	B input
3	GND	—	Ground
4	Y	O	Output
5	V _{CC}	—	Power

(1) Signal Types: I = Input, O = Output, I/O = Input or Output

5 Specifications

5.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted) ⁽¹⁾

		MIN	MAX	UNIT
V_{CC}	Supply voltage	−0.5	7	V
V_I ⁽²⁾	Input voltage	−0.5	7	V
V_O ⁽²⁾	Output voltage	−0.5	$V_{CC} + 0.5$	V
I_{IK}	Input clamp current	$(V_I < 0)$		−20 mA
I_{OK}	Output clamp current	$(V_O < 0 \text{ or } V_O > V_{CC})$		±20 mA
I_O	Continuous output current	$(V_O = 0 \text{ to } V_{CC})$		±25 mA
	Continuous current through V_{CC} or GND			±50 mA
T_J	Maximum junction temperature			150 °C
T_{stg}	Storage temperature	−65	150	°C

(1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

(2) The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

5.2 ESD Ratings

		VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±2000
		Charged-device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾	±1000

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

5.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted) ⁽¹⁾

		MIN	MAX	UNIT
V_{CC}	Supply voltage	2	5.5	V
V_{IH}	High-level input voltage	$V_{CC} = 2 \text{ V}$	1.5	V
		$V_{CC} = 3 \text{ V}$	2.1	
		$V_{CC} = 5.5 \text{ V}$	3.85	
V_{IL}	Low-level input voltage	$V_{CC} = 2 \text{ V}$	0.5	V
		$V_{CC} = 3 \text{ V}$	0.9	
		$V_{CC} = 5.5 \text{ V}$	1.65	
V_I	Input voltage	0	5.5	V
V_O	Output voltage	0	V_{CC}	V
I_{OH}	High-level output current	$V_{CC} = 2 \text{ V}$	−50	μA
		$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$	−4	mA
		$V_{CC} = 5 \text{ V} \pm 0.5 \text{ V}$	−8	
I_{OL}	Low-level output current	$V_{CC} = 2 \text{ V}$	50	μA
		$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$	4	mA
		$V_{CC} = 5 \text{ V} \pm 0.5 \text{ V}$	8	
$\Delta t/\Delta v$	Input transition rise or fall rate	$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$	100	ns/V
		$V_{CC} = 5 \text{ V} \pm 0.5 \text{ V}$	20	

5.3 Recommended Operating Conditions (続き)

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

		MIN	MAX	UNIT
T _A	Operating free-air temperature	−40	125	°C

- (1) All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. See the TI application report, *Implications of Slow or Floating CMOS Inputs*, [SCBA004](#).

5.4 Thermal Information

THERMAL METRIC ⁽¹⁾		SN74AHC1G00			UNIT
		DBV (SOT-23)	DCK (SC70)	DRL (SOT)	
		5 PINS	5 PINS	5 PINS	
R _{θJA}	Junction-to-ambient thermal resistance	278	289.2	256	°C/W
R _{θJC(top)}	Junction-to-case (top) thermal resistance	180.5	205.8	130	°C/W
R _{θJB}	Junction-to-board thermal resistance	184.4	176.2	152	°C/W
ψ _{JT}	Junction-to-top characterization parameter	115.4	117.6	9.9	°C/W
ψ _{JB}	Junction-to-board characterization parameter	183.4	175.1	152	°C/W
R _{θJC(bot)}	Junction-to-case (bot) thermal resistance	N/A	N/A	N/A	°C/W

- (1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application report, [SPRA953](#).

5.5 Electrical Characteristics

over operating free-air temperature range (unless otherwise noted)

PARAMETER ⁽¹⁾	TEST CONDITIONS		V _{CC}	MIN	TYP	MAX	UNIT
V _{OH} High level output voltage	I _{OH} = −50 μA	T _A = 25°C	2 V	1.9	2		V
		T _A = −40°C to +85°C		1.9			
		T _A = −40°C to +125°C		1.9			
		T _A = 25°C	3 V	2.9	3		
		T _A = −40°C to +85°C		2.9			
		T _A = −40°C to +125°C		2.9			
		T _A = 25°C	4.5 V	4.4	4.5		
		T _A = −40°C to +85°C		4.4			
		T _A = −40°C to +125°C		4.4			
	I _{OH} = −4 mA	T _A = 25°C	3 V	2.58			
		T _A = −40°C to +85°C		2.48			
		T _A = −40°C to +125°C		2.48			
	I _{OH} = −8 mA	T _A = 25°C	4.5 V	3.94			
		T _A = −40°C to +85°C		3.8			
		T _A = −40°C to +125°C		3.8			

5.5 Electrical Characteristics (続き)

over operating free-air temperature range (unless otherwise noted)

PARAMETER ⁽¹⁾	TEST CONDITIONS		V _{CC}	MIN	TYP	MAX	UNIT
V _{OL} Low level output voltage	I _{OL} = 50 μ A	T _A = 25°C	2 V			0.1	V
		T _A = –40°C to +85°C				0.1	
		T _A = –40°C to +125°C				0.1	
		T _A = 25°C	3 V			0.1	
		T _A = –40°C to +85°C				0.1	
		T _A = –40°C to +125°C				0.1	
		T _A = 25°C	4.5 V			0.1	
		T _A = –40°C to +85°C				0.1	
		T _A = –40°C to +125°C				0.1	
	I _{OL} = 4 mA	T _A = 25°C	3 V			0.36	
		T _A = –40°C to +85°C				0.44	
		T _A = –40°C to +125°C				0.44	
I _I Input leakage current	V _I = 5.5 V or GND	T _A = 25°C	0 V to 5.5 V			±0.1	μ A
		T _A = –40°C to +85°C				±1	
		T _A = –40°C to +125°C				±1	
I _{CC} Supply current	V _I = V _{CC} or GND, I _O = 0	T _A = 25°C	5.5 V			1	μ A
		T _A = –40°C to +85°C				10	
		T _A = –40°C to +125°C				10	
C _i Input Capacitance	V _I = V _{CC} or GND	T _A = 25°C	5 V		2	10	pF
		T _A = –40°C to +85°C				10	
		T _A = –40°C to +125°C				10	

(1) Recommended T_A = –40°C to +125°C

5.6 Switching Characteristics: V_{CC} = 3.3 V ± 0.3 V

over recommended operating free-air temperature range, V_{CC} = 3.3 V ± 0.3 V (unless otherwise noted) (see [Load Circuit and Voltage Waveforms](#))

PARAMETER	FROM (INPUT)	TO (OUTPUT)	OUTPUT CAPACITANCE	T _A ⁽¹⁾	MIN	TYP	MAX	UNIT
t _{PLH}	A or B	Y	C _L = 15 pF	25°C		5.5	7.9	ns
				−40°C to +85°C	1		9.5	
				−40°C to +125°C	1		10.5	
t _{PHL}				25°C		5.5	7.9	
				−40°C to +85°C	1		9.5	
				−40°C to +125°C	1		10.5	
t _{PLH}	A or B	Y	C _L = 50 pF	25°C		8	11.4	ns
				−40°C to +85°C	1		13	
				−40°C to +125°C	1		14	
t _{PHL}				25°C		8	11.4	
				−40°C to +85°C	1		13	
				−40°C to +125°C	1		14	

(1) Recommended T_A = –40°C to +125°C

5.7 Switching Characteristics: $V_{CC} = 5\text{ V} \pm 0.5\text{ V}$

over recommended operating free-air temperature range, $V_{CC} = 5\text{ V} \pm 0.5\text{ V}$ (unless otherwise noted) (see [Load Circuit and Voltage Waveforms](#))

PARAMETER	FROM (INPUT)	TO (OUTPUT)	OUTPUT CAPACITANCE	T _A ⁽¹⁾	MIN	TYP	MAX	UNIT
t _{PLH}	A or B	Y	C _L = 15 pF	25°C		3.7	5.5	ns
				−40°C to +85°C	1		6.5	
				−40°C to +125°C	1		7	
t _{PHL}				25°C		3.7	5.5	
−40°C to +85°C				1		6.5		
−40°C to +125°C				1		7		
t _{PLH}	A or B	Y	C _L = 50 pF	25°C		5.2	7.5	ns
				−40°C to +85°C	1		6.5	
				−40°C to +125°C	1		9	
t _{PHL}				25°C		5.2	7.5	
−40°C to +85°C				1		6.5		
−40°C to +125°C				1		9		

(1) Recommended $T_A = -40^\circ\text{C}$ to $+125^\circ\text{C}$

5.8 Operating Characteristics

$V_{CC} = 5\text{ V}$, $T_A = 25^\circ\text{C}$

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
C_{pd} Power dissipation capacitance	No load, $f = 1\text{ MHz}$		9.5		pF

5.9 Typical Characteristics

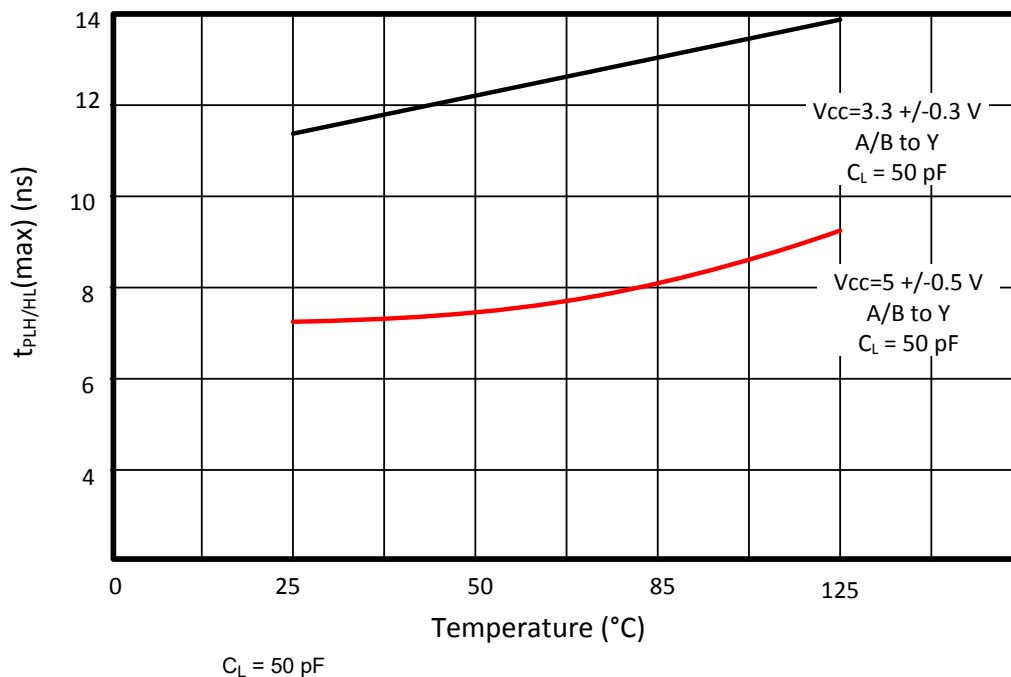
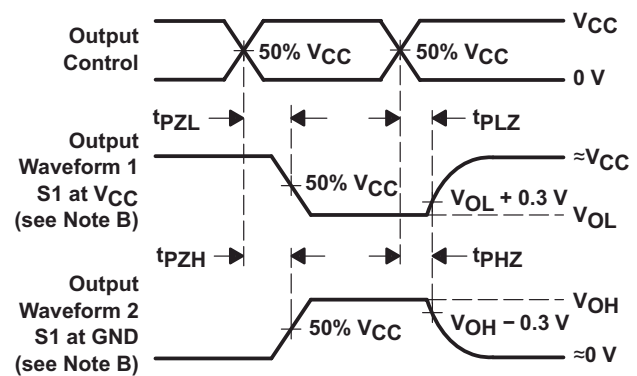
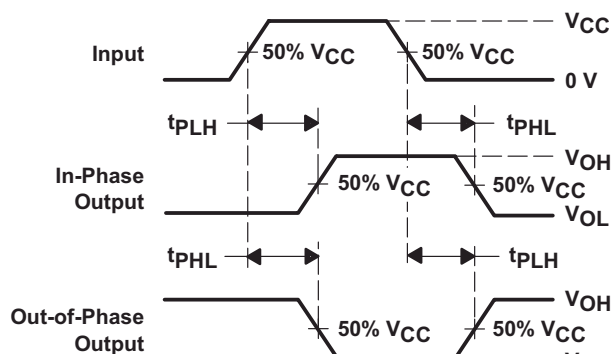
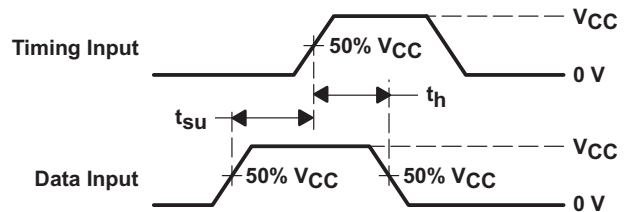
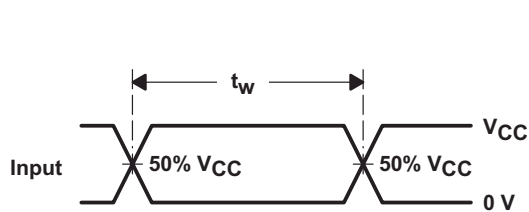
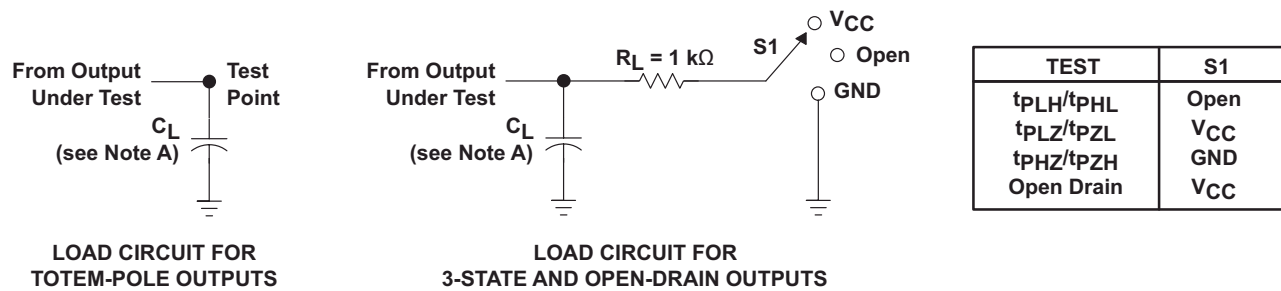


図 5-1. Propagation Delay vs Temperature

6 Parameter Measurement information



- A. C_L includes probe and jig capacitance.
- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: $PRR \leq 1$ MHz, $Z_O = 50 \Omega$, $t_r \leq 3$ ns, $t_f \leq 3$ ns.
- D. The outputs are measured one at a time with one input transition per measurement.
- E. All parameters and waveforms are not applicable to all devices.

图 6-1. Load Circuit and Voltage Waveforms

7 Detailed Description

7.1 Overview

The SN74AHC1G00 device performs the NAND Boolean function $Y = \overline{A \times B}$ or $Y = \overline{A} + \overline{B}$ in positive logic. The device has a wide operating range of V_{CC} from 2 V to 5 V.

7.2 Functional Block Diagram



図 7-1. Logic Diagram (Positive Logic)

7.3 Feature Description

The SN74AHC1G00 device has wide operating voltage range for logic system from 2 V to 5 V. The low propagation delay allows fast switching and higher speeds of operation. In addition, the low power consumption of 10- μ A (maximum) makes this device a good choice for portable and battery power-sensitive applications. The Schmitt trigger action on all inputs have noise rejection capabilities.

7.4 Device Functional Modes

表 7-1. Function Table

INPUTS ⁽¹⁾		OUTPUT ⁽²⁾
A	B	Y
H	H	L
L	X	H
X	L	H

(1) H = High Voltage Level, L = Low Voltage Level, X = Don't Care

(2) H = Driving High, L = Driving Low, Z = High Impedance State

8 Application and Implementation

注

以下のアプリケーション情報は、TI の製品仕様に含まれるものではなく、TI ではその正確性または完全性を保証いたしません。個々の目的に対する製品の適合性については、お客様の責任で判断していただくことになります。お客様は自身の設計実装を検証しテストすることで、システムの機能を確認する必要があります。

8.1 Typical Application

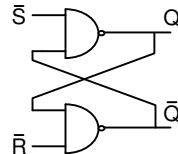


図 8-1. Typical Application

8.1.1 Design Requirements

This SN74AHC1G00 device uses CMOS technology and has balanced output drive. Take care to avoid bus contention because it can drive currents that would exceed maximum limits. The high drive also creates fast edges into light loads. Routing and load conditions must be considered to prevent ringing.

8.1.2 Detailed Design Procedure

- Recommended input conditions:
 - Specified high and low levels. See V_{IH} and V_{IL} in [セクション 5.3](#).
 - Inputs are overvoltage tolerant allowing them to go as high as 5.5 V at any valid V_{CC} .
- Recommended output conditions:
 - Load currents must not exceed 25 mA per output and 50 mA total for the part.
 - Outputs should not be pulled above V_{CC} .

8.1.3 Application Curve

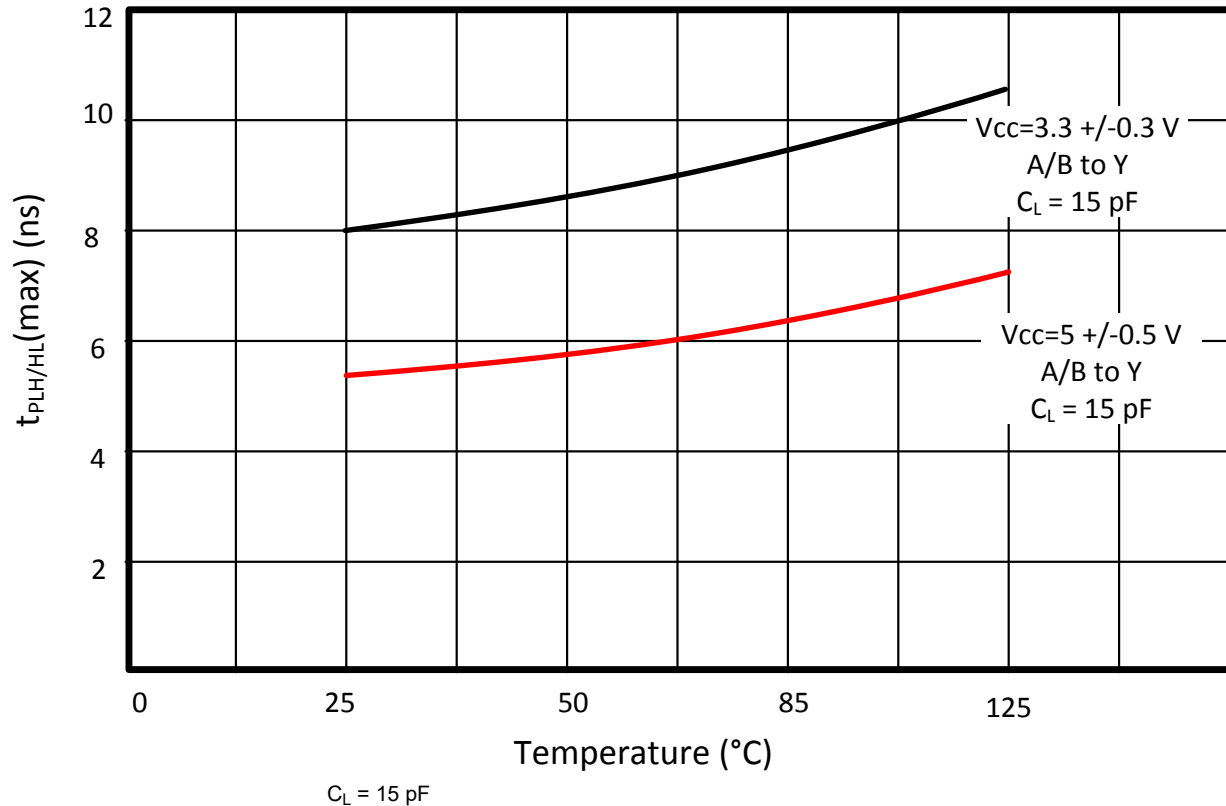


図 8-2. Propagation Delay vs Temperature

8.2 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating located in the [セクション 5.3](#).

Each V_{CC} terminal should have a good bypass capacitor to prevent power disturbance. For devices with a single supply, TI recommends a 0.1- μ F capacitor; if there are multiple V_{CC} terminals, then TI recommends a 0.01- μ F or 0.022- μ F capacitor for each power terminal. Multiple bypass capacitors can be paralleled to reject different frequencies of noise. Frequencies of 0.1 μ F and 1 μ F are commonly used in parallel. The bypass capacitor must be installed as close as possible to the power terminal for best results.

8.3 Layout

8.3.1 Layout Guidelines

When using multiple bit logic devices inputs must not ever float.

In many cases, functions or parts of functions of digital logic devices are unused. For example, when only two inputs of a triple-input AND gate are used or only three of the four buffer gates are used. Such input pins must not be left unconnected because the undefined voltages at the outside connections result in undefined operational states. The following are the rules must be observed under all circumstances.

All unused inputs of digital logic devices must be connected to a high or low bias to prevent them from floating. The logic level that should be applied to any particular unused input depends on the function of the device. Generally they will be tied to GND or V_{CC} whichever make more sense or is more convenient. Floating outputs is generally acceptable, unless the part is a transceiver. If the transceiver has an output enable pin, it disables the outputs section of the part when asserted. This does not disable the input section of the input and output, so they also cannot float when disabled.

8.3.2 Layout Example

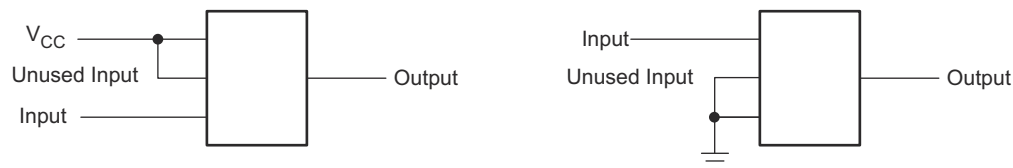


図 8-3. Layout Recommendation

9 Device and Documentation Support

9.1 Documentation Support

9.1.1 Related Documentation

For related documentation, see the following:

- Texas Instruments, [Introduction to Logic application report](#)
- Texas Instruments, [Implications of Slow or Floating CMOS Inputs application note](#)

9.2 ドキュメントの更新通知を受け取る方法

ドキュメントの更新についての通知を受け取るには、www.tij.co.jp のデバイス製品フォルダを開いてください。
[通知] をクリックして登録すると、変更されたすべての製品情報に関するダイジェストを毎週受け取ることができます。変更の詳細については、改訂されたドキュメントに含まれている改訂履歴をご覧ください。

9.3 サポート・リソース

テキサス・インスツルメンツ E2E™ サポート・フォーラムは、エンジニアが検証済みの回答と設計に関するヒントをエキスパートから迅速かつ直接得ることができる場所です。既存の回答を検索したり、独自の質問をしたりすることで、設計に必要な支援を迅速に得ることができます。

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9.4 Trademarks

テキサス・インスツルメンツ E2E™ is a trademark of Texas Instruments.
すべての商標は、それぞれの所有者に帰属します。

9.5 静電気放電に関する注意事項



この IC は、ESD によって破損する可能性があります。テキサス・インスツルメンツは、IC を取り扱う際には常に適切な注意を払うことを推奨します。正しい取り扱いおよび設置手順に従わない場合、デバイスを破損するおそれがあります。

ESD による破損は、わずかな性能低下からデバイスの完全な故障まで多岐にわたります。精密な IC の場合、パラメータがわずかに変化するだけで公表されている仕様から外れる可能性があるため、破損が発生しやすくなっています。

9.6 用語集

テキサス・インスツルメンツ用語集 この用語集には、用語や略語の一覧および定義が記載されています。

10 Revision History

資料番号末尾の英字は改訂を表しています。その改訂履歴は英語版に準じています。

Changes from Revision P (October 2023) to Revision Q (January 2024)	Page
• Updated thermal values for DBV package from RθJA = 240 to 278, RθJC(top) = 174.5 to 180.5, RθJB = 73.7 to 184.4, ΨJT = 54.9 to 115.4, ΨJB = 60.1 to 183.4, RθJC(bot) = N/A, all values in °C/W	5

Changes from Revision O (April 2016) to Revision P (October 2023)	Page
• ドキュメント全体にわたって表、図、相互参照の採番方法を更新	1
• Updated thermal values for DCK package from RθJA = 276.53 to 289.2, RθJC(top) = 118.5 to 205.8, RθJB = 62.8 to 176.2, ΨJT = 6.7 to 117.6, ΨJB = 62.1 to 175.1, RθJC(bot) = N/A, all values in °C/W	5

11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package Pins	Package qty Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
SN74AHC1G00DBVR	Active	Production	SOT-23 (DBV) 5	3000 LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 125	(35XH, 3BSF, A003, A00G, A00J, A00L, A00S)
SN74AHC1G00DBVR.A	Active	Production	SOT-23 (DBV) 5	3000 LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 125	(35XH, 3BSF, A003, A00G, A00J, A00L, A00S)
SN74AHC1G00DBVRG4	Active	Production	SOT-23 (DBV) 5	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	A00G
SN74AHC1G00DBVRG4.A	Active	Production	SOT-23 (DBV) 5	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	A00G
SN74AHC1G00DBVT	Obsolete	Production	SOT-23 (DBV) 5	-	-	Call TI	Call TI	-40 to 125	(A003, A00G, A00J, A00S)
SN74AHC1G00DBVTG4.A	Active	Production	SOT-23 (DBV) 5	250 SMALL T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	A00G
SN74AHC1G00DCKR	Active	Production	SC70 (DCK) 5	3000 LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 125	(1QP, AA3, AAG, AAJ, AAL, AAS)
SN74AHC1G00DCKR.A	Active	Production	SC70 (DCK) 5	3000 LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 125	(1QP, AA3, AAG, AAJ, AAL, AAS)
SN74AHC1G00DCKRE4	Active	Production	SC70 (DCK) 5	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	AA3
SN74AHC1G00DCKRG4	Active	Production	SC70 (DCK) 5	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	AA3
SN74AHC1G00DCKRG4.A	Active	Production	SC70 (DCK) 5	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	AA3
SN74AHC1G00DCKT	Obsolete	Production	SC70 (DCK) 5	-	-	Call TI	Call TI	-40 to 125	(AA3, AAG, AAJ, AAS)
SN74AHC1G00DCKTG4	Active	Production	SC70 (DCK) 5	250 SMALL T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	AA3
SN74AHC1G00DCKTG4.A	Active	Production	SC70 (DCK) 5	250 SMALL T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	AA3
SN74AHC1G00DRLR	Active	Production	SOT-5X3 (DRL) 5	4000 LARGE T&R	Yes	NIPDAU NIPDAUAG	Level-1-260C-UNLIM	-40 to 125	(AAB, AAS)
SN74AHC1G00DRLR.A	Active	Production	SOT-5X3 (DRL) 5	4000 LARGE T&R	Yes	NIPDAUAG	Level-1-260C-UNLIM	-40 to 125	(AAB, AAS)

⁽¹⁾ **Status:** For more details on status, see our [product life cycle](#).

⁽²⁾ **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

⁽³⁾ **RoHS values:** Yes, No, RoHS Exempt. See the [TI RoHS Statement](#) for additional information and value definition.

(4) Lead finish/Ball material: Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

(5) MSL rating/Peak reflow: The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

(6) Part marking: There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

OTHER QUALIFIED VERSIONS OF SN74AHC1G00 :

- Automotive : [SN74AHC1G00-Q1](#)

NOTE: Qualified Version Definitions:

- Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects

TAPE AND REEL INFORMATION



*All dimensions are nominal

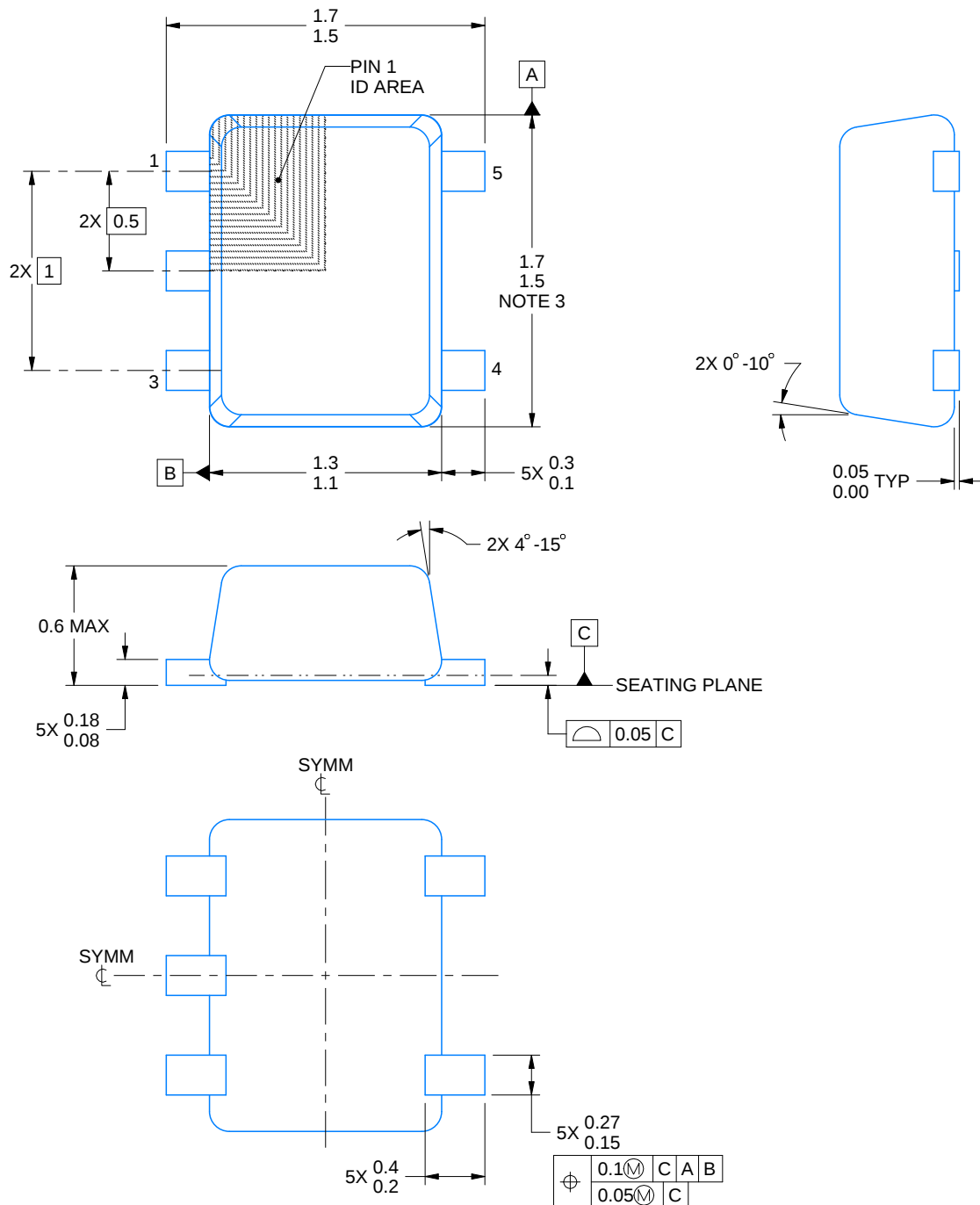
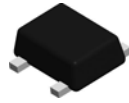
Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74AHC1G00DBVR	SOT-23	DBV	5	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
SN74AHC1G00DBVR	SOT-23	DBV	5	3000	178.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
SN74AHC1G00DBVRG4	SOT-23	DBV	5	3000	178.0	9.0	3.23	3.17	1.37	4.0	8.0	Q3
SN74AHC1G00DCKR	SC70	DCK	5	3000	180.0	8.4	2.3	2.5	1.2	4.0	8.0	Q3
SN74AHC1G00DCKRG4	SC70	DCK	5	3000	178.0	9.2	2.4	2.4	1.22	4.0	8.0	Q3
SN74AHC1G00DCKTG4	SC70	DCK	5	250	178.0	9.2	2.4	2.4	1.22	4.0	8.0	Q3
SN74AHC1G00DRLR	SOT-5X3	DRL	5	4000	180.0	8.4	1.98	1.78	0.69	4.0	8.0	Q3

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74AHC1G00DBVR	SOT-23	DBV	5	3000	210.0	185.0	35.0
SN74AHC1G00DBVR	SOT-23	DBV	5	3000	208.0	191.0	35.0
SN74AHC1G00DBVRG4	SOT-23	DBV	5	3000	180.0	180.0	18.0
SN74AHC1G00DCKR	SC70	DCK	5	3000	210.0	185.0	35.0
SN74AHC1G00DCKRG4	SC70	DCK	5	3000	180.0	180.0	18.0
SN74AHC1G00DCKTG4	SC70	DCK	5	250	180.0	180.0	18.0
SN74AHC1G00DRLR	SOT-5X3	DRL	5	4000	202.0	201.0	28.0



4220753/E 11/2024

NOTES:

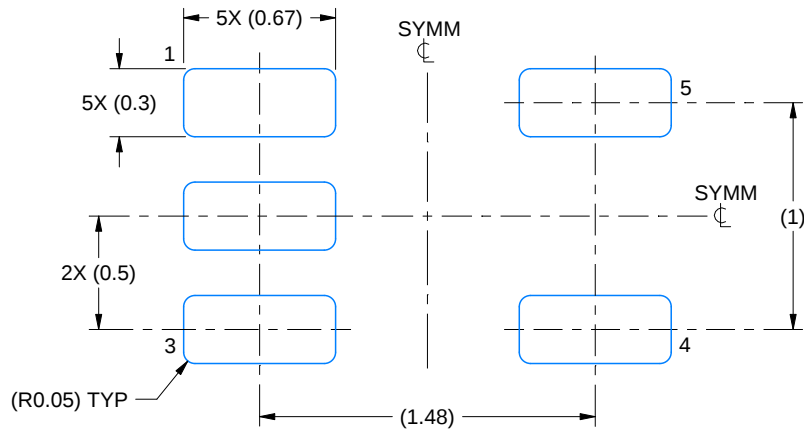
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. Reference JEDEC registration MO-293 Variation UAAD-1

EXAMPLE BOARD LAYOUT

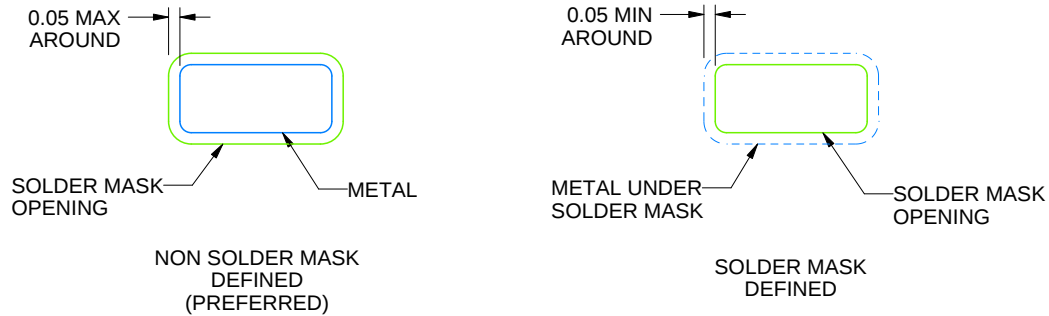
DRL0005A

SOT - 0.6 mm max height

PLASTIC SMALL OUTLINE



LAND PATTERN EXAMPLE
SCALE:30X



SOLDERMASK DETAILS

4220753/E 11/2024

NOTES: (continued)

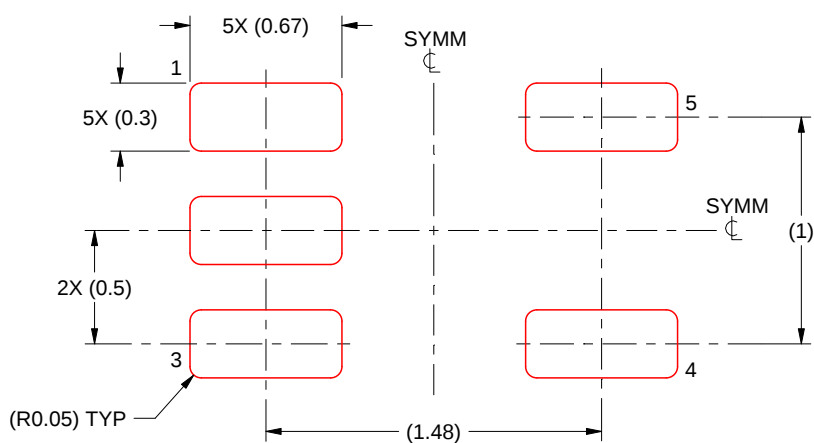
5. Publication IPC-7351 may have alternate designs.
6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

DRL0005A

SOT - 0.6 mm max height

PLASTIC SMALL OUTLINE



SOLDER PASTE EXAMPLE
BASED ON 0.1 mm THICK STENCIL
SCALE:30X

4220753/E 11/2024

NOTES: (continued)

7. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
8. Board assembly site may have different recommendations for stencil design.



4214834/G 11/2024

NOTES:

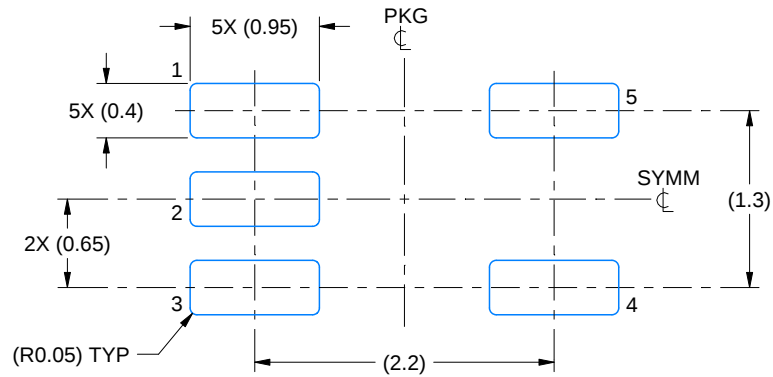
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. Reference JEDEC MO-203.
4. Support pin may differ or may not be present.
5. Lead width does not comply with JEDEC.
6. Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.25mm per side

EXAMPLE BOARD LAYOUT

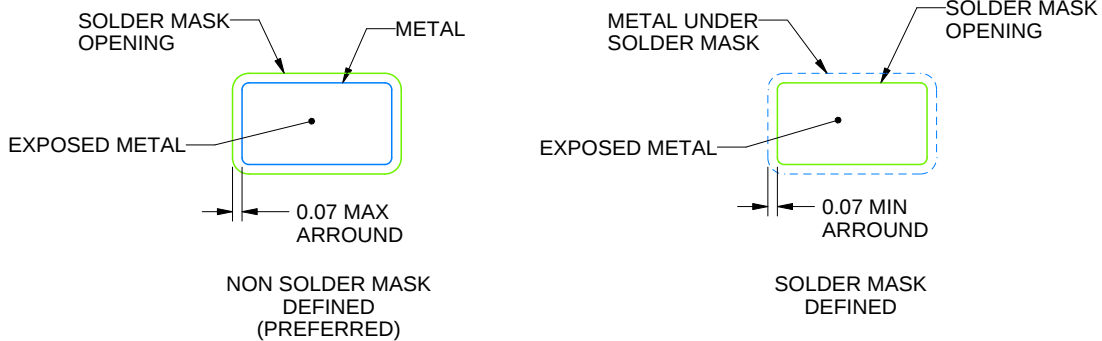
DCK0005A

SOT - 1.1 max height

SMALL OUTLINE TRANSISTOR



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:18X



SOLDER MASK DETAILS

4214834/G 11/2024

NOTES: (continued)

7. Publication IPC-7351 may have alternate designs.
8. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SOLDER PASTE EXAMPLE
 BASED ON 0.125 THICK STENCIL
 SCALE:18X

4214834/G 11/2024

NOTES: (continued)

9. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
10. Board assembly site may have different recommendations for stencil design.

EXAMPLE BOARD LAYOUT

DBV0005A

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:15X



SOLDER MASK DETAILS

4214839/K 08/2024

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

DBV0005A

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE:15X

4214839/K 08/2024

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

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最終更新日：2025 年 10 月